

MITSUBISHI ELECTRIC CORPORATION

	,				 	
	Prepared by	miyazaki, naka	nishi	R		
APPLICATION NOTE	Checked by	Majoshin. THY	om tr	Е		
·	Approved by	5 Parado	2,Hab 06	٧		
		7//				

POWER IGBT MODULE TARGET SPECIFICATION(TENTATIVE)

1. Type

CM100DC-24NFM

2. Structure

Flat Base type (Insulated Package)

3. Application

High frequency switching use

Resonant inverter power supply

4. Outline drawing

Fig.1

5. Maximum ratings (T_i=25°C, unless otherwise specified)

ltem	Symbol	Units	Ratings	Conditions
Collector-emitter voltage	V _{CES}	٧	1200	G-E Short
Gate-emitter voltage	V _{GES}	V	± 20	C-E Short
Collector current	l _c	Α	100	DC, T _C =25°C
Conector current	l _{CM}		200	Pulse ②
Emitter current	l _E ①	Α	100	DC, T _C =25°C
Emilier Current	I _{EM} ①		200	Pulse ②
Maximum power dissipation	P _c ③	w	670	T _C =25°C
Isolation voltage	Viso	٧	2500	Charged part to base plate, AC 1 minute
Junction temperature	Tj	ů	-40 ~ +150	
Storage temperature	Tstg	°C	-40 ~ +125	

6. Mechanical characteristics

ltem	Symbol	Units	Min.	Тур.	Max.	Conditions
Torque strength		N⋅m	3.5		4.5	Main terminals, M6 screw
Torque strength		N∙m	3.5	_	4.5	Mounting holes, M6 screw
Weight		g		400	_	

IGBT MODULE	I2AP-06009	APPLICATION NOTE
	12/11 00000	7.1 TEIO/(110/11/10/12

7. Electrical characteristics (T_i=25°C, unless otherwise specified)

ltem	Symbol	Units	MIN.	TYP.	MAX.	Conditions	
Collector cutoff current	I _{CES}	mΑ	_	-	1	V _{CE} = V _{CES} , V _{GE} =0V	
Gate-emitter threshold voltage	V _{GE(th)}	V	4.5	6	7.5	I _C =10mA, V _{CE} = 10V	
Gate leakage current	I _{GES}	μA		_	0.5	±V _{GE} =V _{GES} , V _{CE} =0V	
Collector-to-emitter		V	. –	3.0	4.5	T _j = 25°C l _C =100A ④	
saturation voltage	V _{CE(sat)}	V	_	3.0	_	T _j =125°C V _{GE} =15V	
Input capacitance	Cies			_	16		
Output capacitance	Coes	∙nF	_	_	1.3	V _{GE} = 0V, V _{CE} =10V	
Reverse transfer capacitance	. Cres			_	0.3		
Total gate charge	Q _G	nC	·	450		V _{CC} =600V, I _C =100A V _{GE} =15V	
Turn-on delay time	td(on)		<u> </u>	• —	100	V _{CC} =600V, I _C =100A	
Turn-on rise time	tr	,	_		50	$V_{GE1}=V_{GE2}=15V, R_{G}=3.1\Omega$	
Turn-off delay time	td(off)	ns	-	_	250	Inductive load switching	
Turn-off fall time	tf		-	-60	200	Operation See Fig.3	
Reverse recovery time	trr ①		_	70	120	I _E =100A	
Reverse recovery charge	Qrr ①	μC	_	6	_	See Fig.4	
Emitter-collector voltage	V _{EC} ①	V	_	2.0	3.0	I _E =100A, V _{GE} =0V	
External gate resistance	R _G	Ω	3.1	. —	31		

- ① I_E, I_{EM}, V_{EC}, t_{rr} & Q_{rr} represent characteristics of the anti-parallel, emitter to collector free-wheel diode.
- ② Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed T_{jmax} rating.
- ③ Junction temperature (T_i) should not increase beyond 150°C.
- ④ Pulse width and repetition rate should be such as to cause negligible temperature rise.

8. Thermal resistance

Item	Symbol	Units	Min.	Тур.	Max.	Conditions
Thermal resistance	R _{th(j-c)}		_	_	0.186	IGBT part *2
Thermal resistance	R _{th(j-c)}	°C/W	_	_	0.28	Free-wheel diode part *2
Contact thermal resistance	R _{th(c-f)}		_	0.02	_	Thermal grease *1, 2 applied

All thermal resistance value above is for 1/2 module.

If use this value, Rth(f-a) should be measured just under the chips.

IGBT MODULE	I2AP-06009	APPLICATION NOTE

^{*1:}Typical value is measured by using Shin-Etsu Chemical Co.,Ltd "G-746".

^{*2:}Tc Tf measured point is just under the chips.

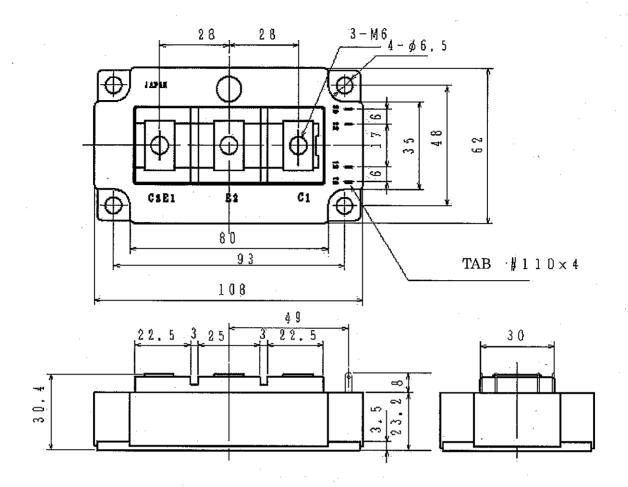


Fig.1 Outline drawing

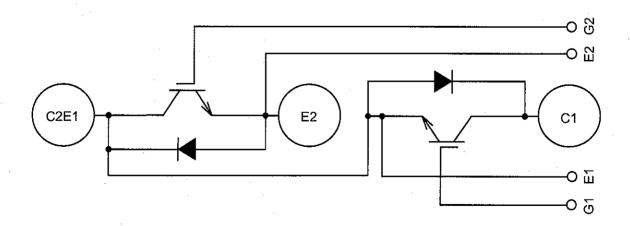


Fig.2 Circuit Diagram

IGBT MODULE	I2AP-06009	APPLICATION NOTE
	(3 / 6)	

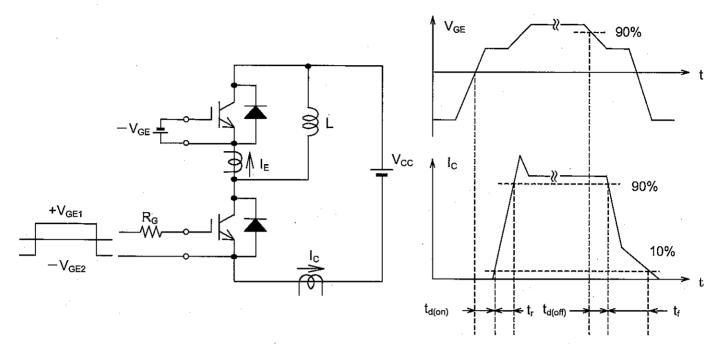


Fig.3 Switching time test circuit and waveforms

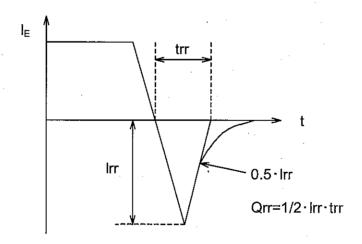


Fig.4 trr, Qrr waveforms

Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

- These materials are intended as a reference to assist our customers in the selection of the Mitsubishi semiconductor product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Mitsubishi Electric Corporation or a third party.
- Mitsubishi Electric Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
- All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Mitsubishi Electric Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for the latest product information before purchasing a product listed herein.
- The information described here may contain technical inaccuracies or typographical errors. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
- Please also pay attention to information published by Mitsubishi Electric Corporation by various means, including the Mitsubishi Semiconductor home page (http://www.mitsubishichips.com/Global/index.html).
- When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
- The prior written approval of Mitsubishi Electric Corporation is necessary to reprint or reproduce in whole or in part these materials.
- Mitsubishi Electric Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
- Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.

 Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for further details on these materials or the products contained therein.

Revision No.	Summary of Changes	Signature	Date
		•	
			·